

64K (8192-word \times 8-bit) SRAM with $\overline{\text{OE}}$, $\overline{\text{CE1}}$, and CE2 Control Pins

Overview

The LC3564CM and LC3564CT-55U/70U are 8192-word × 8-bit asynchronous silicon gate CMOS SRAMs. These are full CMOS type SRAMs that adopt a six-transistor memory cell and feature fast access times, low operating power dissipation, and an ultralow standby current. These SRAMs provide three control signal inputs: an \overline{OE} input for high-speed memory access, and two chip enable lines, $\overline{CE1}$ and CE2, for low power mode and device selection. These means that these SRAMs area ideal for systems that require low power and battery backup, and that they support easy memory expansion. The ultralow standby current that is a feature of these SRAMs allows them to be used with capacitor backup as well. Since these SRAMs support 3-V operation, they are also appropriate for use in portable battery operated systems.

Features

Supply voltage range: 2.7 to 5.5 V
 In 5-V operation mode: 5.0 V ±10%
 In 3-V operation mode: 3.0 V ±10%

• Address access time (t_{AA})

— In 5-V operation mode:

LC3564CM, and CT-55U: 55 ns (max) LC3564CM, and CT-70U: 70 ns (max)

— In 3-V operation mode:

LC3564CM, and CT-70U: 200 ns (max)

- Ultralow standby current
 - In 5-V operation mode: 1.0 μ A (Ta ≤ 70°C),

3.0 μ A (Ta ≤ 85°C)

— In 3-V operation mode: $0.8 \mu A$ (Ta $\leq 70^{\circ}C$),

2.5 μ A (Ta ≤ 85°C)

- Operating temperature range
 - In 5-V operation mode: –40 to 85°C
 - In 3-V operation mode: –40 to 85°C
- Data retention supply voltage: 2.0 to 5.5 V
- All input and output levels:
 - In 5-V operation mode: TTL compatible levels
 - In 3-V operation mode: V_{CC} –0.2 V/0.2 V
- Three control inputs: \overline{OE} , $\overline{CE1}$, and CE2
- Shared input and output pins, three-state outputs
- · No clock required
- Packages

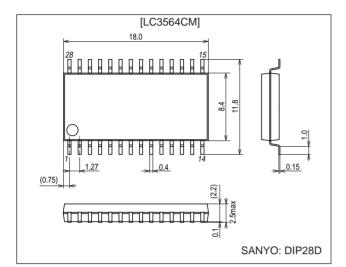
28-pin SOP (450 mil) plastic package: LC3564CM 28-pin TSOP (8 × 13.4 mm) plastic package: LC3564CT

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Package Dimensions

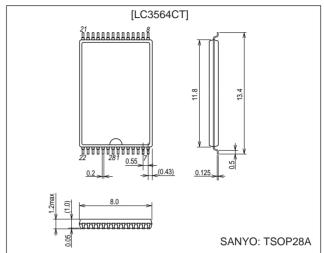
unit: mm

3187B-DIP28D

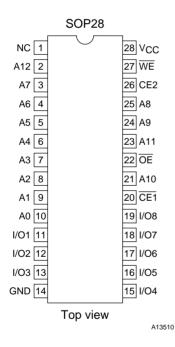


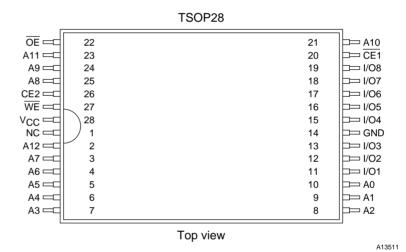
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3221-TSOP28A

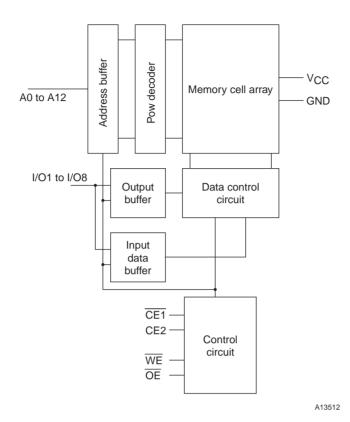


Pin Assignments





Block Diagram



Pin Functions

A0 to A12	Address inputs
WE	Read/write control input
ŌĒ	Output enable input
CE1, CE2	Chip enable inputs
I/O1 to I/O8	Data I/O
V _{CC} , GND	Power supply and ground

Function Table

Mode	CE1	CE2	ŌĒ	WE	I/O	Supply current
Read cycle	L	Н	L	Н	Data output	I _{CCA}
Write cycle	L	Н	Х	L	Data input	I _{CCA}
Output disable	L	Н	Н	Н	High impedance	I _{CCA}
Not selected	Н	Х	X	Х	High impedance	Iccs
inot selected	Х	L	Х	Х	High impedance	Iccs

X : H or L

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC} max		7.0	V
Input voltage	V _{IN}		-0.3* to V _{CC} + 0.3	V
I/O voltage	V _{I/O}		-0.3 to $V_{CC} + 0.3$	V
Operating temperature	Topr		-40 to +85	°C
Storage temperature	Tstg		-55 to +125	°C

Note: For pulse widths less than 30 ns: -3.0 V

Input and Output Capacitances at $Ta = 25^{\circ}C$, f = 1 MHz

Parameter Symbol	Conditions		Unit			
Faianetei	Symbol	Conditions	min	typ	max	Offic
I/O pin capacitance	C _{I/O}	V _{I/O} = 0 V		6	10	pF
Input pin capacitance	C _{IN}	V _{IN} = 0 V		6	10	pF

Note: These parameters are sampled, and are not measured for every unit.

[5-V Operation]

DC Allowable Operating Ranges at $Ta = -40 \text{ to } +85^{\circ}\text{C}, V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$

Parameter Sv		Conditions		Unit		
Faianetei	Symbol	Conditions	min	typ	max	Office
Supply voltage	V _{CC}		4.5	5.0	5.5	V
Input voltage	V _{IH}		2.2		V _{CC} + 0.3	V
input voitage	V _{IL}		-0.3*		+0.8	V

Note: For pulse widths less than 30 ns: -3.0 V

DC Electrical Characteristics at Ta = -40 to $+85^{\circ}C$, $V_{CC} = 4.5$ to 5.5~V

Parameter		Cumphal	Con	ditiono				Ratings		Unit		
Param	eter	Symbol	Conditions		min	typ *	max	Offic				
Input leakage current		ILI	V _{IN} = 0 to V _{CC}				-1.0		+1.0	μA		
I/O leakage current		I _{LO}	$V_{\overline{CE1}} = V_{IH} \text{ or } V_{CE2} = V_{WE} = V_{IL}, V_{I/O} = 0 \text{ to}$		V _{OE} = \	/ _{IH} or	-1.0		+1.0	μA		
Output high-level voltage		V _{OH}	I _{OH} = -1.0 mA				2.4			V		
Output low-level voltage		V _{OL}	I _{OL} = 2.0 mA						0.4	V		
		I _{CCA1}	$V_{CE1} \le 0.2 \text{ V}, V_{CE2} \ge I_{I/O} = 0 \text{ mA}, V_{IN} \le 0.2 \text{ M}$	$V_{CE1} \le 0.2 \text{ V}, V_{CE2} \ge V_{CC} - 0.2 \text{ V}, T_{a} \le 70^{\circ}\text{C}$			0.01	1.0	μA			
	V _{CC} – 0.2 V/0.2 V	-CCA1	$V_{IN} \ge V_{CC} - 0.2 \text{ V}$			Ta ≤ 85°C			3.0	·		
	inputs							ICM, CT-55U			45	
		I _{CCA4}	$V_{CE2} \ge V_{CC} - 0.2 \text{ V},$ $I_{I/O} = 0 \text{ mA},$	cycle	LC3564	ICM, CT-70U			35	mA		
0				1 µs c	ycle			4				
Operating supply current		I _{CCA2}	$V_{\overline{CE1}} = V_{IL}, V_{CE2} = V_{IN}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	/ _{IH} , I _{I/O} :	= 0 mA,				7	mA		
	TTL inputs		V _{CE1} = V _{IL} ,	min	LC3564	ICM, CT-55U			45			
		I _{CCA3}	$V_{CE2} = V_{IH},$ $I_{I/O} = 0 \text{ mA},$ cycle		LC3564	ICM, CT-70U			40	mA		
			DUTY = 100%	1 µs c	ycle			7				
Standby mode supply	V _{CC} – 0.2 V/0.2 V	I _{CCS1}	$V_{CE2} \le 0.2 \text{ V or}$ $V_{CE1} \ge V_{CC} - 0.2 \text{ V}$			Ta ≤ 70°C		0.01	1.0	μA		
current	inputs	10051	1		Ta ≤ 85°C			3.0				
	TTL inputs	I _{CC2}	V _{CE2} = V _{IL} or V _{CE1} =	· V _{IH} , V _I	N = 0 to	V _{CC}			2.0	mA		

Note *: Reference values at $V_{CC} = 5 \text{ V}$, $Ta = 25^{\circ}C$

AC Electrical Characteristics at $Ta = -40~to~+85^{\circ}C,\,V_{CC} = 4.5~to~5.5~V$

Parameter	Conditions
[AC Test Conditions]	
Input pulse voltage	$V_{IH} = 2.4 \text{ V}, V_{IL} = 0.6 \text{ V}$
Input rise and fall times	5 ns
Input and output timing level	1.5 V
Output load	LC3564CM and CT-55U/70U: 30 pF + 1 TTL gate (Including the jig capacitance.)

Read Cycle

Parameter	Symbol	-55	5U	-70	ıU	Unit
		min	max	min	max	
Read cycle time	t _{RC}	55		70		ns
Address access time	t _{AA}		55		70	ns
CE1 access time	t _{CA1}		55		70	ns
CE2 access time	t _{CA2}		55		70	ns
OE access time	t _{OA}		30		35	ns
Output hold time	t _{OH}	10		10		ns
CE1 output enable time	t _{COE1}	5		10		ns
CE2 output enable time	t _{COE2}	5		10		ns
OE output enable time	tooe	5		5		ns
CE1 output disable time	t _{COD1}		20		30	ns
CE2 output disable time	t _{COD2}		20		30	ns
OE output disable time	t _{OOD}	-	20		25	ns

Write Cycle

Parameter	Symbol	-55	-55U		U	Unit
		min	max	min	max	
Write cycle time	t _{WC}	55		70		ns
Address setup time	t _{AS}	0		0		ns
Write pulse width	t _{WP}	40		50		ns
CE1 setup time	t _{CW1}	50		60		ns
CE2 setup time	t _{CW2}	50		60		ns
Write recovery time	t _{WR}	0		0		ns
CE1 write recovery time	t _{WR1}	0		0		ns
CE2 write recovery time	t _{WR2}	0		0		ns
Data setup time	t _{DS}	25		35		ns
Data hold time	t _{DH}	0		0		ns
CE1 data hold time	t _{DH1}	0		0		ns
CE2 data hold time	t _{DH2}	0		0		ns
WE output enable time	t _{WOE}	5		5		ns
WE output disable time	t _{WOD}		30		30	ns

[3-V Operation]

DC Allowable Operating Ranges at $Ta = -40 \ to \ +85^{\circ}C, \ V_{CC} = 2.7 \ to \ 3.3 \ V$

Parameter Symbol		Conditions		Unit		
Farameter	Symbol	Conditions	min	typ	max	Offic
Supply voltage	V _{CC}		2.7	3.0	3.3	V
Input voltage	V_{IH}		V _{CC} - 0.2		V _{CC}	V
input voitage	V_{IL}		0		0.2	V

DC Electrical Characteristics at Ta = -40 to $+85^{\circ}C$, $V_{CC} = 2.7$ to 3.3~V

Parameter		Cumbal	Con	ditions			Ratings			Unit
Falaili	etei	Symbol	Con	iuitions			min	typ *	max	Offic
Input leakage current		ILI	V _{IN} = 0 to V _{CC}				-1.0		+1.0	μA
I/O leakage current		I _{LO}	$V_{\overline{CE1}} = V_{IH}$ or $V_{CE2} = V_{IL}$ or $V_{\overline{OE}} = V_{IH}$ or $V_{\overline{WE}} = V_{IL}$, $V_{I/O} = 0$ to V_{CC}		-1.0		+1.0	μA		
Output high-level voltage		V _{OH}	$I_{OH} = -0.5 \text{ mA}$				V _{CC} - 0.2			V
Output low-level voltage		V _{OL}	I _{OL} = 1.0 mA				0.2	V		
			$V_{CE1} \le V_{IL}, V_{CE2} \ge V_{II}$ $I_{I/O} = 0 \text{ mA}, V_{IN} \le V_{II}$	$V_{CE1} \le V_{IL}, V_{CE2} \ge V_{IH},$ $Ta \le 70^{\circ}C$		Ta ≤ 70°C		0.01	0.8	
		I _{CCA1}	$V_{IN} \ge V_{IH}$	_ 01		Ta ≤ 85°C			2.5	μA
Operation supply current	V _{CC} – 0.2 V/0.2 V inputs	I _{CCA4}	$V_{\overline{CE1}} \le V_{IL},$ $V_{CE2} \ge V_{IH},$ $I_{I/O} = 0 \text{ mA},$	min cycle	LC3564	CM, CT-70U			20	mA
			DUTY = 100%	1 µs c	ycle			3		mA
Standby mode supply	V _{CC} – 0.2 V/0.2 V	lassi	V _{CE2} ≤ 0.2 V or V _{CE1} ≥ V _{IH}		Ta ≤ 70°C		0.01	0.8	μA	
current	inputs	I _{CCS1}	VCE1 ≤ VIH VCE2 ≥ VIH			Ta ≤ 85°C			2.5	μΑ

Note *: Reference values at V_{CC} = 3 V, Ta = 25°C

AC Electrical Characteristics at $Ta = -40~to~+85^{\circ}C,\,V_{CC} = 2.7~to~3.3~V$

Parameter	Conditions
[AC Test Conditions]	
Input pulse voltage	$V_{IH} = V_{CC} - 0.2 \text{ V}, V_{IL} = 0.2 \text{ V}$
Input rise and fall times	10 ns
Input and output timing level	1.5 V
Output load	LC3564CM, CT-70U : 30pF (Including the jig capacitance.)

Read Cycle

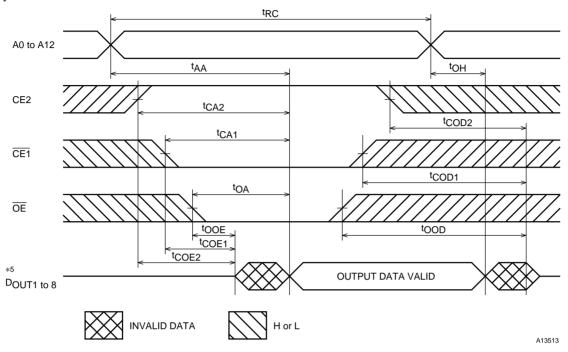
Parameter		LC3564C		
	Symbol	-10		Unit
		min	max	
Read cycle time	t _{RC}	200		ns
Address access time	t _{AA}		200	ns
CE1 access time	t _{CA1}		200	ns
CE2 access time	t _{CA2}		200	ns
OE access time	t _{OA}		100	ns
Output hold time	t _{OH}	20		ns
CE1 output enable time	t _{COE1}	20		ns
CE2 output enable time	t _{COE2}	20		ns
OE output enable time	t _{OOE}	10		ns
CE1 output disable time	t _{COD1}		60	ns
CE2 output disable time	t _{COD2}		60	ns
OE output disable time	t _{OOD}		50	ns

Write Cycle

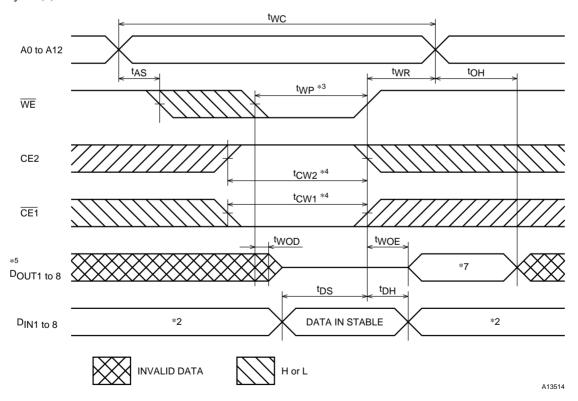
	Symbol	LC3564CN		
Parameter		-70	Unit	
		min	max	
Write cycle time	t _{WC}	200		ns
Address setup time	t _{AS}	0		ns
Write pulse width	t _{WP}	140		ns
CE1 setup time	t _{CW1}	150		ns
CE2 setup time	t _{CW2}	0		ns
Write recovery time	t _{WR}	0		ns
CE1 write recovery time	t _{WR1}	0		ns
CE2 write recovery time	t _{WR2}	130		ns
Data setup time	t _{DS}	0		ns
Data hold time	t _{DH}	0		ns
CE1 data hold time	t _{DH1}	0		ns
CE2 data hold time	t _{DH2}	10		ns
WE output enable time	t _{WOE}			ns
WE output disable time	t _{WOD}		60	ns

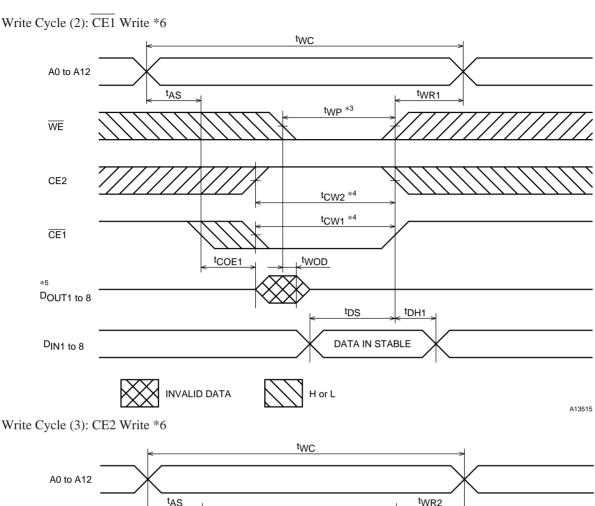
Timing Charts

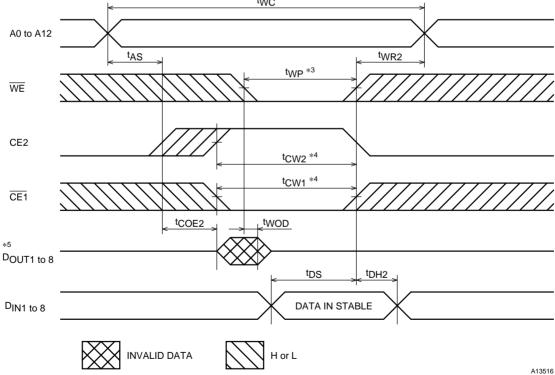
Read Cycle *1



Write Cycle (1): WE Write *6







Notes: 1. Hold WE high during the read cycle.

- 2. Applications must not apply reverse phase signals to the D_{OUT} pins when those pins are in the output state.

 3. The time tWP is the period when CE1 and WE are low and CE2 is high, and is defined as the time from the fall of WE until either CE1 or WE rises, or CE2 falls, whichever occurs first.
- 4. The times t_{CW1} and t_{CW2} are periods when $\overline{\text{CE1}}$ and $\overline{\text{WE}}$ are low and CE2 is high. They are defined as the times from the fall of $\overline{\text{CE1}}$ or the rise of CE2 to the rise of $\overline{\text{CE1}}$ and $\overline{\text{WE}}$, or the fall of CE2, whichever occurs first.
- $5. \ \underline{\text{The D}_{\text{OUT}}} \ \text{pins will be in the high-impedance state if either } \overline{\text{OE}} \ \text{is high, } \overline{\text{CE1}} \ \text{is high, CE2 is low, or } \overline{\text{WE}} \ \text{is low.}$
- 6. OE must be held either at V_{IH} or V_{IL} during the write cycle.
- 7. The D_{OUT} pins have the same phase as the write cycle write data.

Data Retention Characteristics at $Ta = -40 \text{ to } +85^{\circ}\text{C}$

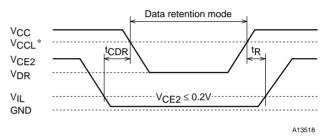
Parameter	Symbol	Conditions		Ratings			Unit
Farameter		Conditions			typ	max	Offic
Data retention supply voltage	V _{DR}	$\begin{split} &V_{CE2} \leq 0.2 \text{ V or} \\ &V_{\overline{CE1}} \geq V_{CC} - 0.2 \text{ V}, V_{CE2} \geq V_{CC} - 0.2 \text{ V} \end{split}$		2.0		5.5	μA
Data retention supply current I _{CCDR}		or $V_{\overline{CE1}} \ge V_{CC} - 0.2 \text{ V}$,	Ta ≤ 70°C			0.8	μΑ
	CCDR		Ta ≤ 85°C			2.5	
Chip enable setup time	t _{CDR}			0			ns
Chip enable hold time	t _R			t _{RC} *			ns

Note *: t_{RC} is the read cycle time.

Data Retention Waveforms (1): CE1 Control

 $\begin{array}{c|c} & & & & & & & \\ VCC & & & & & & \\ VCCL^* & & & & & \\ \hline V_{IH} & & & & & \\ \hline V_{DR} & & & & \\ \hline V_{\overline{CE}1} & & & & \\ \hline V_{\overline{CE}1} \geq V_{CC} - 0.2V & & \\ \hline GND & & & & \\ \hline \end{array}$

Data Retention Waveforms (2): CE2 Control



Note *:In 5-V operation: 4.5 V In 3-V operation: 2.7 V

Notes on Circuit Design

When actually design a circuit using these devices, take the following points into consideration and design the circuit so that none of the maximum rating items are ever exceeded.

- Variations in the supply voltage
- · Variations in the electrical characteristics of components such as semiconductor devices, resistors, and capacitors.
- Ambient temperature
- Variations in input and clock signals
- Possible application of abnormal pulses

Also, these devices must be operated within the ranges stipulated in the allowable operating ranges.

If CMOS IC input pins are left open, intermediate potential input voltages may occur leading to incorrect operation due to through currents or other phenomenon. Applications must handle unused input pins appropriately.

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